

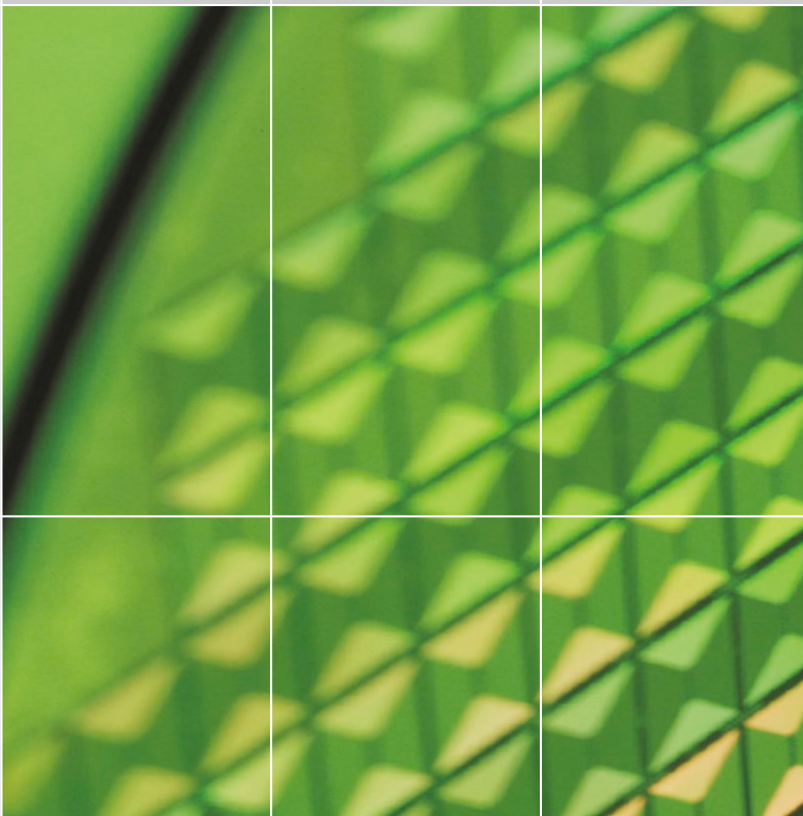
SEMICONDUCTOR

PCB/CHIP PACKAGING

INDUSTRIAL/MEDICAL

## SIRD™ Metrology System

Scanning infrared depolarization tool  
for monitoring of process related stress in wafers



- Defect mapping/imaging and screening
- Process quality monitoring
- Process tool verification
- Yield improvement
- <7 min measuring time per wafer possible
- In-line capability

**PVA**  **TePla**

The SIRD™ depolarization imager is a noncontact, nondestructive evaluation tool for the characterization of mechanical stress fields in semiconductor material. Stress fields cause birefringence due to the photoelastic effect in semiconducting material. The SIRD™ tool, acting as a polarimeter, visualizes the stress by measuring and recording the depolarization of incident polarized laser light after its transition through the wafer. Monitoring of process induced stress and process induced defects by their stress fields plays an important role for rapid process development in semiconductor technology. The way through the learning curve can be considerably accelerated by applying nondestructive evaluation methods like scanning infrared depolarization. In addition, a continuous monitoring of the defect generation with standard recipes in high temperature tools prevents parameter deviations and yield reduction. The SIRD™ is capable of generating a full wafer image of the stress fields for silicon wafers up to 300 mm diameter in less than 7 minutes providing a lateral resolution of 0.1 mm.

#### Wafer manufacturing

- Defect screening and wafer sorting in early stages of wafer manufacturing
- Slipline detection in case of rapid thermal annealing procedures
- Monitoring of temperature gradients by induced stress evaluation
- Monitoring of technological procedures during wafer design
- Fracture prevention
- Final quality testing

#### IC manufacturing

##### Input control and sorting

- Slipline detection for high temperature processes
- Fracture prevention
- Monitoring of process induced stress mainly in RTP, ion implantation, diffusion and epitaxy trouble shooting

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## Technical Data

### Measurement Module

Measurement unit:

Infrared transmission plane polarimeter (wavelength 1.3 μm)

Scanning unit:

Two axis stage (rotation and radial translation) with edge grabber for Wafer support

Control unit:

Industrial PC (IBM AT compatible, Windows operating system)

Housing:

Stainless steel, clean room class 1 compatible

### Handling Module

Handling unit:

Robot with prealigner and slot scanner

Robot end effectors: vacuum chuck, material: VESPEL

Edge gripper optional

Support ring with 3-point wafer edge support (3 x 0.5 mm)

Load port:

Open carrier load port, SMIF-load port, FOUP available

### Filter Fan Unit

Dimension:

524 x 755 x 550 mm

Filter type:

H14 or U16

### Software

SIRDtec, SIRDinspect, SIRDview

### Operation Conditions and Parameters

Wafer sizes:

50, 75, 100, 125, 150, 200, 300 mm

Resistivity

>6 m Ω cm

Semiconductor material: Silicon, III-V Compounds and others

Surface:

No metallic layers, no restriction by roughness

Wafer support:

Support ring with 3-point wafer edge support (3 x 0.5 mm)

Maximum lateral resolution:

100 μm

Sensitivity:

Shear stress equivalent >10<sup>-5</sup>, stress detection limit in Si-wafer of 620 μm thickness >6 kPa

Wafer area:

Full wafer image (no signal in the edge facette of the wafer),

Radial extension of the scanning area selectable by recipe

Throughput:

Full wafer image (normal resolution, 300 mm-wafer), 5 min

10 wafer/h (typical)

Laser safety:

Class 1

### Installation Requirements and Physical Dimensions

Foot print:

Module 1,350 x 700 mm

Total weight of connected

modules:

700 kg

Media supply:

Electricity: voltage 230 VAC, frequency 50 Hz standard, power <1.5 kVA

Compressed air: pressure 6 bar, flow 200 l/min

Vacuum: pressure <20 kPa, flow 4 m<sup>3</sup>/h

### Environmental Conditions

Temperature:

22°C ± 1°C

Environmental factors:

3K2 according DIN IEC 721/3-3

Relative humidity:

<60%

Floor:

Flat, air exhaust to bottom